



| Pin | Symbol | | Function |
|---------|--------|---|---|
| 1 | OUT | 0 | Output to the load. The pin 1 and 5 must be shorted with each |
| | | | other especially in high current applications!*) |
| 2 | IN | Ι | Input, activates the power switch in case of short to ground |
| Tab/(3) | Vbb | + | Positive power supply voltage, the tab is shorted to this pin. |
| 4 | IS | S | Diagnostic feedback providing a sense current proportional to the load current; high current on failure (see Truth Table on page 6) |
| 5 | OUT | 0 | Output to the load. The pin 1 and 5 must be shorted with each |
| | | | other especially in high current applications!*) |

*) Not shorting all outputs will considerably increase the on-state resistance, reduce the peak current capability and decrease the current sense accuracy

Maximum Ratings at $T_j = 25$ °C unless otherwise specified

| Parameter | Symbol | Values | Unit |
|---|-------------------------------------|-------------------------|------|
| Supply voltage (overvoltage protection see page 4) | V _{bb} | 36 | V |
| Supply voltage for full short circuit protection | V _{bb} | 24 ¹⁾ | V |
| (see also diagram on page 9) T_{j} =-40150 °C: | | | |
| Load dump protection $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{s}}$, $U_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}} = 2 \Omega$, $R_{\text{L}} = 2.7 \Omega$, $t_{\text{d}} = 200 \text{ ms}$, IN= low or high | V _{Load dump²)} | 60 | V |
| Load current (Short-circuit current, see page 4) | <i>I</i> | self-limited | А |
| Operating temperature range | T _j | -40+150 | °C |
| Storage temperature range | T _{stg} | -55+150 | |
| Power dissipation (DC) TC \leq 25°C | P _{tot} | 42 | W |
| Inductive load switch-off energy dissipation, single pulse U=12V, I=10A, L=3mH T_j =150 °C: | E _{AS} | 0.15 | J |
| Electrostatic discharge capability (ESD) (Human Body Model) acc. ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF | V _{ESD} | 4.0 | kV |
| Current through input pin (DC) | I _{IN} | +15, -100 | mA |
| Current through current sense pin (DC) | I _{IS} | +15, -100 | |
| see internal circuit diagrams page 7 | | | |

¹⁾ Short circuit is tested with $100m\Omega$ and $20\mu H$

²⁾ $V_{Load dump}$ is set-up without the DUT connected to the generator per ISO 7637-1 and DIN 40839



Thermal Characteristics

| Parameter and Conditi | Symbol | Values | | | Unit | |
|-----------------------|--|---------------------|-----|-----|------|-----|
| | | - | min | typ | max | |
| Thermal resistance | chip - case: | $R_{\rm thJC}^{3)}$ | | | 1.5 | K/W |
| ju | unction - ambient (free air): | $R_{ m thJA}$ | | 80 | | |
| SME |) version, device on PCB ⁴): | | | 45 | | |

Electrical Characteristics

| Parameter and Conditions | Symbol | Values | | | Unit |
|---|--------|--------|-----|-----|------|
| at T_{j} = -40°C150°C, V_{bb} = 12 V unless otherwise specified | | min | typ | max | |

Load Switching Capabilities and Characteristics

| On-state resistance (pin 3 to pin 1,5) | | | | | |
|---|------------------------|-----|-----|-----|------|
| $V_{\rm IN}=0, \ I_{\rm L}=5 \ {\rm A}$ $T_{\rm j}=25 \ {\rm ^{\circ}C}:$ | R _{ON} | | 13 | 16 | mΩ |
| <i>T</i> _j =150 °C: | | | 25 | 31 | |
| Output voltage drop limitation at small load currents (Tab to pin 1,5) T_{j} =-40150 °C: | V _{ON(NL)} | | 50 | | mV |
| Nominal load current (Tab to pin 1,5) | | | | | Α |
| ISO Proposal: <i>T</i> _C =85°C, <i>V</i> _{ON} ≤0.5V, <i>T</i> _j ≤150°C | I _{L(ISO)} | 21 | 25 | | |
| SMD ⁴): <i>T</i> _A =85°C, <i>V</i> _{ON} ≤0.5V, <i>T</i> _j ≤150°C | I _{L(nom)} | 6.2 | 7.6 | | |
| Turn-on time I _{IN} I to 90% V _{OUT} : | <i>t</i> on | 150 | | 410 | μs |
| Turn-off time $I_{IN} \perp$ to 10% V_{OUT} : | <i>t</i> off | 70 | | 410 | |
| <i>R</i> _L = 2,5Ω, <i>T</i> _j =-40150 °C | | | | | |
| Slew rate on | dV/dt _{on} | 0.1 | | 1 | V/µs |
| 10 to 30% <i>V</i> _{OUT} , <i>R</i> _L = 2.5 Ω, <i>T</i> _j =-40150 °C | | | | | |
| Slew rate off 70 to 40% V_{OUT} , $R_{L} = 2.5 \Omega$, T_{j} =-40150 °C | -d V/dt _{off} | 0.1 | | 1 | V/µs |

³⁾ Thermal resistance R_{thCH} case to heatsink (about 0.5 ... 0.9 K/W with silicone paste) not included!

⁴⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



| Parameter and Conditions | Symbol | Values | | Unit | |
|---|--------|--------|-----|------|--|
| at T_{j} = -40°C150°C, V_{bb} = 12 V unless otherwise specified | | min | typ | max | |

Operating Parameters

| Operating voltage (V _{IN} =0V) | | V _{bb(on)} | 5.0 | | 36 | V |
|---|----------------------------------|----------------------|-----|-----|-----|----|
| Undervoltage shutdown ⁵⁾ | | V _{bIN(u)} | 1.5 | 3.0 | 4.5 | V |
| Undervoltage restart of charge | ge pump (V _{IN} =0V) | V _{bb(ucp)} | 3.0 | 4.5 | 6.0 | V |
| Overvoltage protection ⁶⁾ | | V _{Z,IN} | 61 | 68 | | V |
| <i>I</i> _{bb} =15 mA | | | | | | |
| Standby current | <i>T</i> _j =-40+25°C∶ | I _{bb(off)} | | 2 | 5 | μΑ |
| / _{IN} =0 | <i>T</i> j=150°C: | | | 4 | 8 | |

Protection Functions 7)

| Short circuit current limit (Tab to pin 1,5) | | | | | |
|---|---------------------|----------------|----------------|-------------------|----|
| V _{ON} =8V, time until limitation max. 300µs | | | | | |
| <i>T</i> _j =-40°C: <i>T</i> _j =25°C: <i>T</i> _j =+150°C: | I _{L(SC)} | 35 35 35 | 75 65 65 | 110 110 125 | A |
| Repetitive short circuit current limit, $T_j = T_{jt}$ | I _{L(SCr)} | | 65 | | А |
| Output clamp (inductive load switch off) at $V_{OUT} = V_{bb} - V_{ON(CL)}$ (e.g. overvoltage) $I_L = 40 \text{ mA}^{-8}$ | V _{ON(CL)} | 38 | 42 | 48 | V |
| Thermal overload trip temperature | T _{jt} | 150 | | | °C |
| Thermal hysteresis | ΔT_{jt} | | 10 | | K |

Reverse Battery

| Reverse battery voltage | -V _{bb} | | 20 | V |
|---|----------------------|------------------|----------------|----|
| On-state resistance (pin 1,5 to pin 3) | | | | |
| V_{bb} = -8V, V_{IN} = 0, I_L = -5 A, R_{IS} = 1 k Ω , T_j =25 °C: V_{bb} = -12V, V_{IN} = 0, I_L = -5 A, R_{IS} = 1 k Ω , T_j =25 °C: T_j =150 °C: | R _{ON(rev)} | 16 25 | 22 19 32 | mΩ |
| Integrated resistor in V_{bb} line | R _{bb} | 200 | | Ω |

⁵⁾ VbIN=Vbb-VIN see diagram on page 11.

⁶⁾ see also $V_{ON(CL)}$ in circuit diagram on page 7.

⁷⁾ Integrated protection functions are designed to prevent IC destruction under fault condition described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not for continuous repetitive operation.

⁸⁾ see also page 12.



Diagnostic Characteristics

| Current sense ratio, static on-condition | <i>k</i> _{ILIS} | | 8200 | | |
|---|-----------------------------|--------------|--------------|----------------|----|
| $k_{\text{ILIS}} = I_{\text{L}} : I_{\text{IS}}$ $V_{\text{ON}} < 1.5 \text{ V}, V_{\text{IS}} < V_{\text{OUT}} - 5 \text{ V}, V_{\text{bIN}} > 4.5 \text{ V}^{9}$ | | | | | |
| $V_{ON} < 1.5 \text{ V}, V_{IS} < V_{OU} = 5 \text{ V}, V_{BIN} > 4.5 \text{ V}^{-3}$ | | | | | |
| $IL = 20A, Tj = -40^{\circ}C:$ | | 7400 | 8300 | 9100 | |
| Tj = +25°C: Tj = +150°C: | | 7500 7500 | 8300 8200 | 9100 8800 | |
| IL = 5A, Tj = -40°C: | | 6800 | 8300 | 9700 | |
| $T_1 = +25^{\circ}C$: | | 7200 | 8300 | 9300 | |
| $Tj = +150^{\circ}C:$ | | 7200 | 8200 | 9000 | |
| IL = 2.5A, Tj = -40°C: Tj = +25°C: | | 6800 6800 | 8500 8500 | 10000 9800 | |
| $T_{j} = +150^{\circ}C$: | | 6800 | 8100 | 9200 | |
| $IL = 1A, Tj = -40^{\circ}C$: | | 6800 | 8600 | 10500 | |
| Tj = +25°C: Tj = +150°C: | | 6800 6800 | 8600 8600 | 10500 10500 | |
| $I_{\rm IN} = 0$ (e.g. during de-energising of inductive loads): | | | n.a. | | |
| Sense current under fault conditions; | | | | | |
| V_{DS} >1.5V, typ. T_{j} = -40+150°C: | I _{IS,fault} | 2.5 | 4 | | mA |
| Fault-Sense signal delay after negative input slope | <i>t</i> delay(fault) | | | 0.8 | ms |
| Current sense leakage current | | | | | |
| $I_{\rm IN} = 0$ | I _{IS(LL)} | | | 0.5 | μA |
| $V_{\rm IN} = 0, \ I_{\rm L} = 0$ | | | 4 | 12 | |
| Current sense settling time to <i>I</i> _{IS static} ±10% after | | | | | |
| positive input slope, $I_{L} = 0 \int 20 \text{ A}^{-10}$ | <i>t</i> _{son(IS)} | | | 400 | μs |
| | | | | | |
| Overvoltage protection | | | | | |
| $I_{\rm bb} = 15 \mathrm{mA}$ $T_{\rm i} = -40+150^{\circ}\mathrm{C}$: | V _{bIS(Z)} | 61 | 68 | | V |

Input

| Required current capability of input switch $T_j = -40+150^{\circ}C$: | I _{IN(on)} | 0.7 | 1.2 | mA |
|---|----------------------|---------|-----|----|
| Maximum input current for turn-off $T_j = -40+150^{\circ}C$: | I _{IN(off)} | | 50 | μA |

⁹⁾ If V_{ON} is higher, the sense current is no longer proportional to the load current due to sense current saturation.

¹⁰) not subject to production test, specified by design



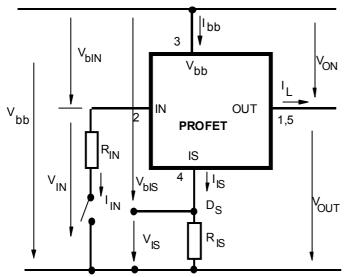


Truth Table

| | Input | Output | Current |
|----------------------|---------|--------|-------------------------------|
| | Current | | Sense |
| | level | level | lis |
| Normal | L | L | 0 |
| operation | Н | Н | nominal |
| Overload | L | L | 0 |
| | Н | Н | I _{ISfault} |
| Short circuit to GND | L | L | 0 |
| | Н | L | I _{ISfault} |
| Overtemperature | L | L | 0 |
| | Н | L | I _{ISfault} |
| Short circuit to Vbb | L | Н | 0 |
| | Н | Н | <nominal<sup>11</nominal<sup> |
| Open load | L | Z | 0 |
| | Н | Н | 0 |

L = "Low" Level H = "High" Level Z = high impedance, potential depends on external circuit

Terms

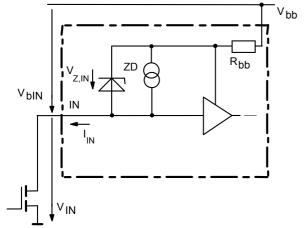


Two or more devices can easily be connected in parallel to increase load current capability.

¹¹⁾ Low ohmic short to $V_{\rm bb}$ may reduce the output current $I_{\rm L}$ and therefore also the sense current $I_{\rm IS}$.



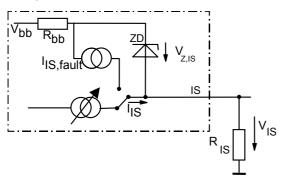
Input circuit (ESD protection)



ESD-Zener diode: 68 V typ., max 15 mA;

Current sense output

Normal operation

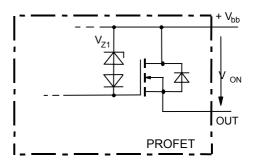


 $V_{Z,IS} = 68 V$ (typ.), $R_{IS} = 1 k\Omega$ nominal (or $1 k\Omega / n$, if n devices are connected in parallel). $I_S = I_L / k_{ilis}$ can be only driven by the internal circuit as long as $V_{out} - V_{IS} > 5V$. If you want to measure load currents

up to $I_{\rm L(M)}$, R_{IS} should be less than ${V_{bb}$ - $5V\over I_{L(M)}/K_{ilis}}$

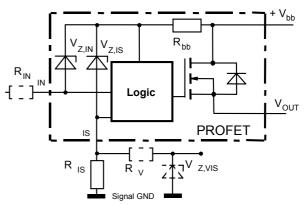
Note: For large values of R_{IS} the voltage V_{IS} can reach almost V_{bb}. See also overvoltage protection. If you don't use the current sense output in your application, you can leave it open.

Inductive and overvoltage output clamp



 V_{ON} is clamped to $V_{ON(CI)} = 42 V$ typ.

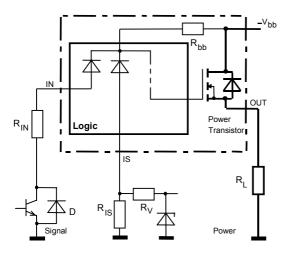
Overvoltage protection of logic part



$$\begin{split} R_{bb} = &200\,\Omega \text{ typ.}, \ V_{Z,IN} = V_{Z,IS} = &68 \text{ V typ.}, \ R_{IS} = &1 \text{ k}\Omega \\ \text{nominal. Note that when overvoltage exceeds 73 V typ.} \\ \text{a voltage above 5V can occur between IS and GND, if} \\ R_V, \ V_{Z,VIS} \text{ are not used.} \end{split}$$



Reversave[™] (Reverse battery protection)



 $R_{V} \ge 1 k\Omega$, $R_{IS} = 1 k\Omega$ nominal. Add R_{IN} for reverse battery protection in applications with V_{bb} above 16V;

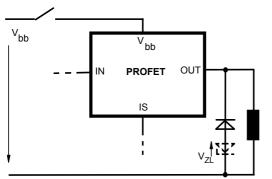
recommended value: $\frac{1}{R_{IN}} + \frac{1}{R_{IS}} + \frac{1}{R_V} = \frac{0.05A}{|V_{bb}| - 12V}$

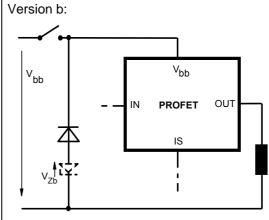
To minimise power dissipation at reverse battery operation, the summarised current into the IN and IS pin should be about 50mA. The current can be provided by using a small signal diode D in parallel to the input switch, by using a MOSFET input switch or by proper adjusting the current through R_{IS} and R_{V} . Since the current through R_{bb} generates additional heat in the device, this has to be taken into account in the overall thermal considerations.

V_{bb} disconnect with energised inductive load

Provide a current path with load current capability by using a diode, a Z-diode, or a varistor. ($V_{ZL} < 73$ V or $V_{Zb} < 30$ V if R_{IN}=0). For higher clamp voltages currents at IN and IS have to be limited to 250 mA.

Version a:

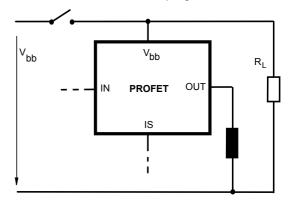




Note that there is no reverse battery protection when using a diode without additional Z-diode V_{ZL} , V_{Zb} .

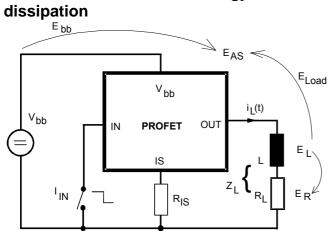
Version c:

Sometimes a necessary voltage clamp is given by non inductive loads R_L connected to the same switch and eliminates the need of clamping circuit:





Inductive load switch-off energy



Energy stored in load inductance:

$$E_{\rm L} = \frac{1}{2} \cdot {\rm L} \cdot {\rm I}_{\rm L}^2$$

While demagnetising load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt,$$

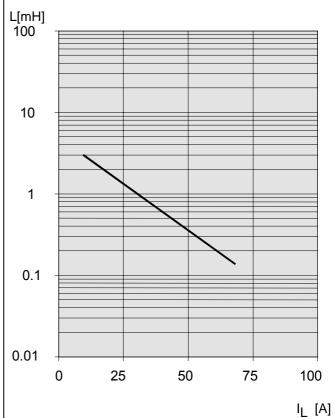
with an approximate solution for $R_L > 0 \Omega$:

$$E_{\text{AS}} = \frac{I_{\text{L}} \cdot L}{2 \cdot R_{\text{L}}} (V_{\text{bb}} + |V_{\text{OUT}(\text{CL})}|) ln (1 + \frac{I_{\text{L}} \cdot R_{\text{L}}}{|V_{\text{OUT}(\text{CL})}|})$$

The device is not suitable for permanent PWM with inductive loads if active clamping occurs every cycle.

Maximum allowable load inductance for a single switch off

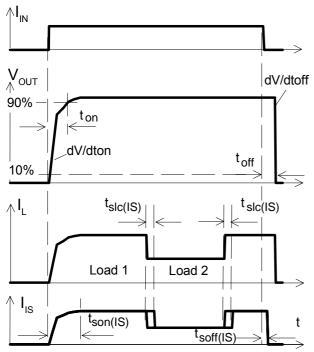
 $L = f(\tilde{I_L})$; T_{j,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω





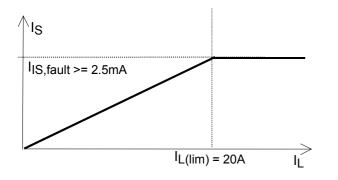
Timing diagrams

Figure 1a: Switching a resistive load, change of load current in on-condition:



The sense signal is not valid during a settling time after turn-on/off and after change of load current.

Figure 1b: typical behaviour of sense output:



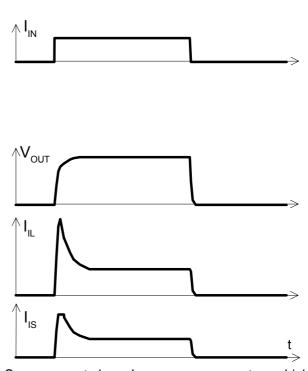
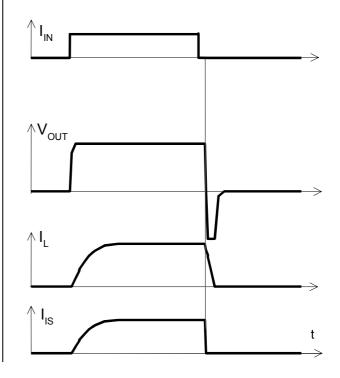


Figure 2a: Switching motors and lamps:

Sense current above I_{IS,fault} can occur at very high inrush currents.

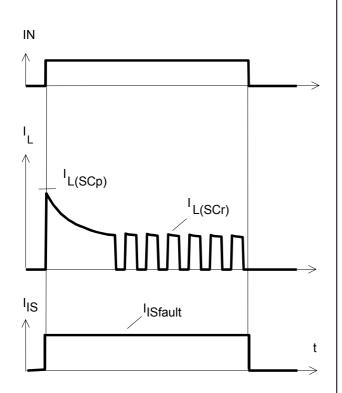
Figure 2b: Switching an inductive load:

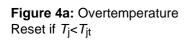




Data Sheet BTS 443 P

Figure 3a: Short circuit:





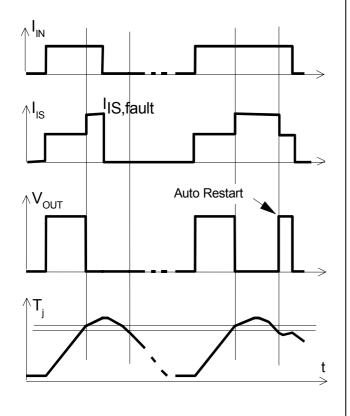
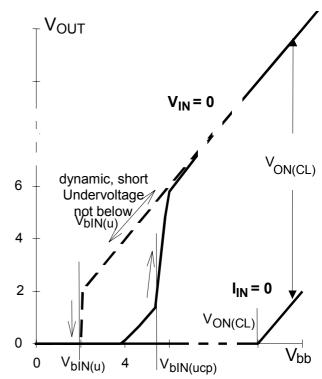
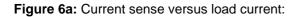
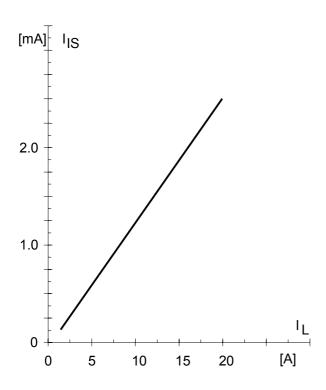


Figure 5a: Undervoltage restart of charge pump, overvoltage clamp









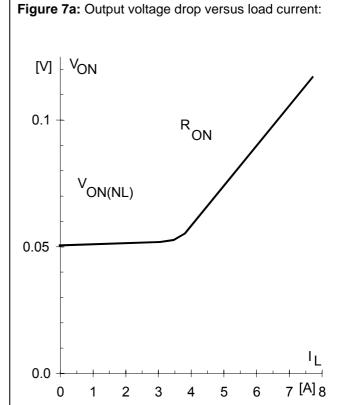
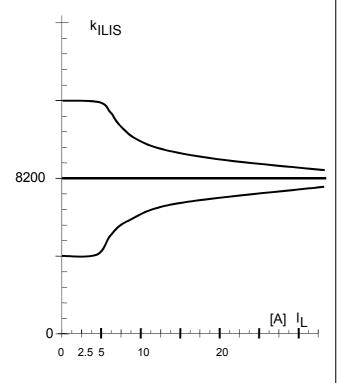


Figure 6b: Current sense ratio¹²:



¹² ⁾ This range for the current sense ratio refers to all devices. The accuracy of the $k_{\rm ILIS}$ can be raised by means of calibration the value of $k_{\rm ILIS}$ for every single device.



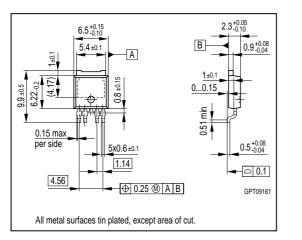


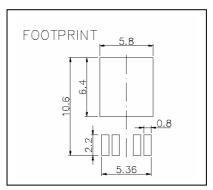
Package and Ordering Code

All dimensions in mm

D-Pak-5 Pin: TO-252-5-1

| Sales Code | BTS443P |
|---------------|------------------|
| Ordering code | Q67060-S7404-A 2 |





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